

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SB857, 2SB858

Silicon PNP Triple Diffused

RENESAS

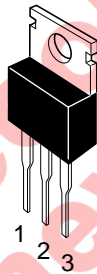
ADE-208-859 (Z)
1st. Edition
September 2000

Application

Low frequency power amplifier complementary pair with 2SD1133 and 2SD1134

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings (T_a = 25°C)

Item	Symbol	Ratings		Unit
		2SB857	2SB858	
Collector to base voltage	V _{CBO}	-70	-70	V
Collector to emitter voltage	V _{CEO}	-50	-60	V
Emitter to base voltage	V _{EBO}	-5	-5	V
Collector current	I _C	-4	-4	A
Collector peak current	I _{C(peak)}	-8	-8	A
Collector power dissipation	P _C *1	40	40	W
Junction temperature	T _j	150	150	°C
Storage temperature	T _{stg}	-45 to +150	-45 to +150	°C

Note: 1. Value at T_C = 25°C

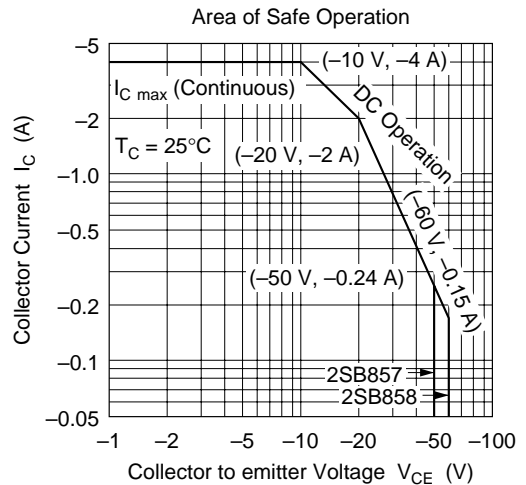
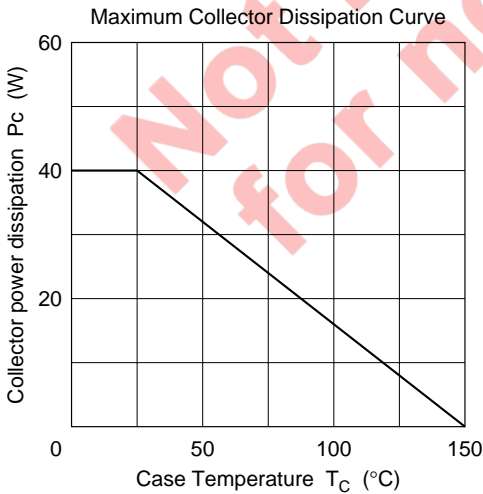
2SB857, 2SB858

Electrical Characteristics (Ta = 25°C)

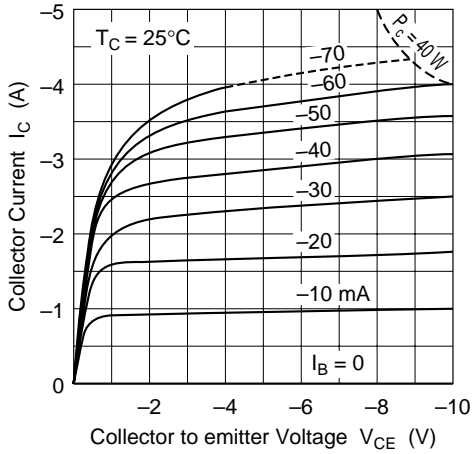
Item	Symbol	2SB857			2SB858			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-70	—	—	-70	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-50	—	—	-60	—	—	V	$I_C = -50 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-1	—	—	-1	μA	$V_{CB} = -50 \text{ V}, I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	320	60	—	320		$V_{CE} = I_C = -1 \text{ A}^{*2}$
	h_{FE2}	35	—	—	35	—	—		$-4 \text{ V}, I_C = -0.1 \text{ A}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-1	—	—	-1	V	$I_C = -2 \text{ A}, I_B = -0.2 \text{ A}^{*2}$
Base to emitter voltage	V_{BE}	—	—	-1	—	—	-1	V	$V_{CE} = -4 \text{ V}, I_C = -1 \text{ A}^{*2}$
Gain bandwidth product	f_T	—	15	—	—	15	—	MHz	$V_{CE} = -4 \text{ V}, I_C = -0.5 \text{ A}^{*2}$

Notes: 1. The 2SB857 and 2SB858 are grouped by h_{FE1} as follows.
2. Pulse test

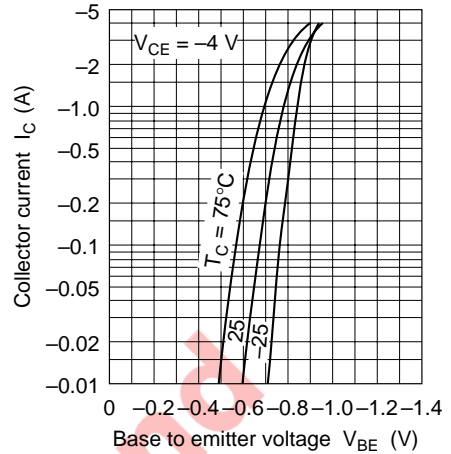
B	C	D
60 to 120	100 to 200	160 to 320



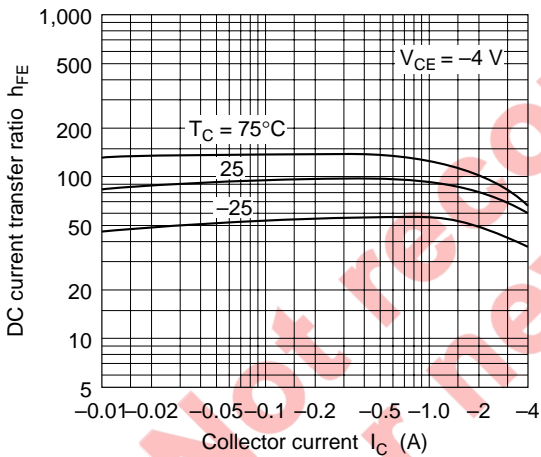
Typical Output Characteristics



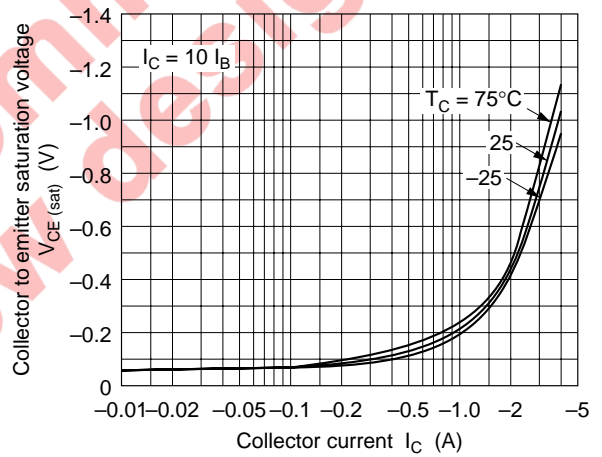
Typical Transfer Characteristics



DC Current Transfer Ratio vs. Collector Current



Collector to Emitter Saturation Voltage vs. Collector Current



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U S A
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Domacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071